**Observation of vacancies during Zn diffusion in GaP** 

# R. Krause-Rehberg<sup>1</sup>, V. Bondarenko<sup>1</sup>, N.A. Stolwijk<sup>2</sup>, J. Pöpping<sup>2</sup>, T.E.M. Staab<sup>3</sup>

<sup>1</sup>Univ. Halle, <sup>2</sup>Univ. Münster, <sup>3</sup>Univ. Bonn



- 1. Zn-diffusion experiments in GaP
- 2. The EPOS positron source at Research Center Rossendorf



# Sample conditions

Experiment	sample	treatment	remarks	
	А	as-grown GaP reference	negligible low dislocation density, no	
Reference		sample	extended defects	
	В	Reference annealing:	defined P vapor pressure, but no Zn in	
		95.1 h at 907°C	ampoule	
	С	Zn diffusion annealing:	defined P vapor pressure, Zn vapor	
Diffusion95.1 h at 907°Cprexperimentsan		95.1 h at 907°C	pressure obtained by adding GaP:Zn to the	
			ampoule	
	D	Zn Diffusion annealing:	defined P vapor pressure, Zn was added as	
		95.1 h at 907°C	an elementary powder to the ampoule	

- Samples were quenched to RT water during diffusion
- Main difference of diffusion experiments: Zn vapor pressure varies due to different Zn source
- Diffusion profiles are distinctly different



# Zn diffusion profiles by SIMS

• Zn diffusion profiles obtained by SIMS at beveled samples (wedge angle 6°)







## **Positron lifetime results**



- both reference samples: no trapping
- distinct vacancy signal only after Zn in-diffusion
- sample D: almost complete positron trapping at RT
- defect-related lifetime:  $\tau_v$  = 282 ps
- outward relaxation is expected for both vacancies:
- V<sub>Ga</sub> -> 3.8% and V<sub>P</sub> -> 6.1%
  (G. Schwarz et al., Phys. Rev. 1998)
- lifetimes were theoretically calculated taking into account the relaxation



## **Positron lifetime results**



• defect-related lifetime:  $\tau_v$  = 282 ps

Defect	e <sup>+</sup> lifetime	remarks	
	in ps		
GaP bulk	220		
$V_{Ga}$	258	unrelaxed	
	270	3.8% outward	
		relaxation	
V <sub>P</sub>	244	unrelaxed	
	271	6.1% outward	
		relaxation	
V <sub>P</sub> -Zn <sub>Ga</sub>	274	6.1% outward	
		relaxation	
V <sub>P</sub> -V <sub>Ga</sub>	307	unrelaxed	

\* from lifetime: no decision between  $V_{\mbox{\scriptsize Ga}}$  and  $V_{\mbox{\scriptsize P}}$ 



# **Doppler Coincidence Experiments**

- DBCS was used to study the chemical environment of the detected monovacancy
- surprise: although complete trapping -> high-momentum Doppler spectrum close to reference sample
- comparison with theoretically calculated spectra required





# **Doppler Coincidence Experiments**





# **Doppler Coincidence Experiments**



## Conclusion

- During Zn in-diffusion: vacancies are formed
- concentration is much higher than thermal vacancies
- Vacancy is located in P sublattice
- V<sub>p</sub> should be positive -> thus a defect complex is most probably observed
- best candidate: V<sub>P</sub>-Zn<sub>Ga</sub>

planned experiment:

- comparison of vacancy depth profile with Zn-diffusion profile
- we will use Munich Microbeam and the beveled SIMS samples





# The EPOS positron source at Research Center Rossendorf

- main experiment: Radiation source ELBE (Electron Linac with high Brilliance) and low Emittance
- primary electron beam (40 MeV x 1 mA = 40 kW) is already available
- main goal: IR Free-electron Laser
- very interesting time structure: cw-mode of short bunches





#### Ground plan of the ELBE hall



![](_page_10_Picture_2.jpeg)

![](_page_11_Figure_0.jpeg)

- Construcion work started
- Financing ...

![](_page_11_Figure_3.jpeg)

![](_page_12_Figure_0.jpeg)

 positron lab in ELBE hall already under construction

Positron Lab -

X-ray Lab

concrete screening of Cave 111b (location of e<sup>+</sup> converter)

![](_page_13_Picture_0.jpeg)

![](_page_13_Picture_1.jpeg)

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### **EPOS (ELBE Positron Source)**

![](_page_14_Figure_1.jpeg)

#### **Detector system**

- 3 experiments: lifetime spectroscopy (16 BaF<sub>2</sub> detectors); Doppler coincidence (2 Ge detectors), and AMOC (1 Ge and 1 BaF<sub>2</sub> detector)
- digital detection system:
  - lifetime: almost nothing to adjust; time scale exactly the same for all detectors; easy realization of coincidence
  - Doppler: better energy resolution and pile-up rejection expected

![](_page_15_Figure_5.jpeg)

![](_page_16_Picture_0.jpeg)

	1. Year	2. Year	3. Year
Laboratory			
Simulation e <sup>+</sup> converter			
Simulation beam			
Converter chamber and vacuum system in tunnel			
Screening of converter chamber			
First chopper / buncher			
Test converter / beam transport			
Vacuum system completion			
Conventional source chamber			
2. Chopper / buncher			
Sample chamber			
Completion of beam electronics			
Test transport system			
Detector system and software			
Automation			
Software lifetime / Doppler spectra			
Optimization of time resolution			

![](_page_16_Picture_2.jpeg)

### Thank you for your attention!

This presentation can be found as pdf-file on our Websites: http://positron.physik.uni-halle.de http://positronannihilation.net

contact: mail@KrauseRehberg.de